

# EPIGAP Optronik GmbH

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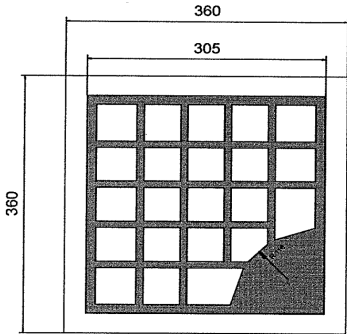
## Data Sheet

### LED Chip Infrared

### EOLC-1720-17-1

Rev. 03, 2017

Radiation	Type	Electrodes
Infrared	InGaAs, MQW	P (anode) up

	<b>typ. dimensions (μm)</b>
	typ. thickness: 260 μm anode: gold alloy, 1.5 μm cathode: gold alloy, 0.5 μm

### Maximum Ratings

T<sub>amb</sub> = 25°C, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward current (DC)		I <sub>F</sub>			100	mA
Peak forward current	t <sub>p</sub> ≤ 50 μs, t <sub>p</sub> /T = 1/2	I <sub>FM</sub>			200	mA

### Optical and Electrical Characteristics

T<sub>amb</sub> = 25°C, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	I <sub>F</sub> = 20 mA	V <sub>F</sub>		0.7		V
Forward voltage	I <sub>F</sub> = 100 mA	V <sub>F</sub>		0.9		V
Reverse voltage	I <sub>R</sub> = 100 μA	V <sub>R</sub>	5			V
Radiant power*	I <sub>F</sub> = 20 mA	Φ <sub>e</sub>		0.8		mW
Radiant power*	I <sub>F</sub> = 100 mA	Φ <sub>e</sub>		2.8		mW
Peak wavelength	I <sub>F</sub> = 20 mA	λ <sub>p</sub>		1720		nm
FWHM	I <sub>F</sub> = 20 mA	Δλ <sub>0.5</sub>		100		nm
Switching time	I <sub>F</sub> = 20 mA	t <sub>r</sub> , t <sub>f</sub>		10		ns

\*Measured on bare chip on TO-18 header

### Packing

Chips on adhesive film with wire-bond side top

Art. No. 113 042



We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.